Elektronische Bauelemente

PZTA94

PNP Transistor

Epitaxial Planar Transistor

RoHS Compliant Product

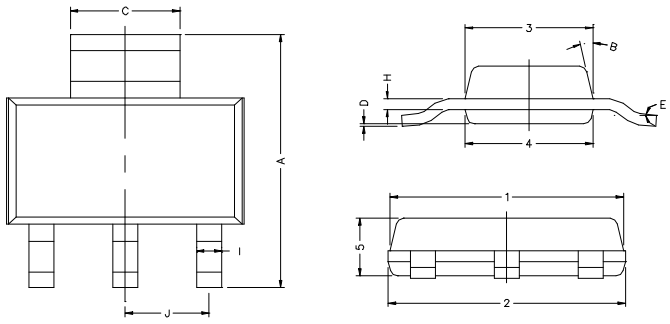
Description

The PZTA94 is designed for application requires high voltage.

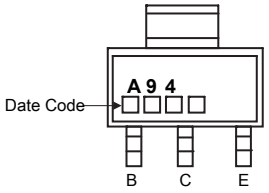
Features

*High Current Gain: I_C=300mA at 25°C
*High Voltage: V_{CEO}=400V (min) at I_C=1mA
*Complementary With PZTA44

SOT-223



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80



ABSOLUTE MAXIMUM RATINGS Ta=25°C

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-400	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-500	mA
P_D	Total Power Dissipation	2	W
T_J,T_{stg}	Junction and Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS Tamb=25°C unless otherwise specified

Parameter	Symbol	Min	Typ.	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-400	-	-	V	I_C=-100μA,I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-400	-	-	V	I_C=-1mA,I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-6	-	-	V	I_E=-100μA,I_C=0
Collector-Base Cutoff Current	I_{CBO}	-	-	-100	nA	V_{CB}=-400V,I_E=0
Emitter-Base Cutoff Current	I_{EBO}	-	-	-100	nA	V_{BE}=-6V,I_C=0
Collector-Base Cutoff Current	I_{CES}	-	-	-500	nA	V_{CE}=-400V,V_{BE}=0
Collector Saturation Voltage	*V_{CE}(sat)1	-	-	-350	mV	I_C=-1mA,I_B=-0.1mA
	*V_{CE}(sat)2	-	-	-500	mV	I_C=-10mA,I_B=-1mA
	*V_{CE}(sat)3	-	-	-750	mV	I_C=-50mA,I_B=-5mA
Base Satruation Voltage	V_{BE}(sat)	-	-	-750	mV	I_C=-10mA,I_B=-1mA
DC Current Gain	*h_{FE}1	40	-	-		V_{CE}=-10V, I_C=-1mA
	*h_{FE}2	50	-	300		V_{CE}=-10V, I_C=-10mA
	*h_{FE}3	45	-	-		V_{CE}=-10V, I_C=-50mA
	*h_{FE}4	40	-	-		V_{CE}=-10V, I_C=-100mA

*Pulse width≦380μs, Duty Cycle≦2%

Characteristics Curve